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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	Unknown
Filing Date	December 11, 2001
First Named Inventor	IZUO
Group Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	401479/AOYAMA

[illegible][illegible]

OTHER - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Doc. No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number (s), publisher, city and/or country where published.	Translation	
			Yes	No++
DN	A 11	H.W. LAU et al.; "High aspect ratio silicon pillars fabricated by electrochemical etching and oxidation of macroporous silicon", <u>Elsevier Science S.A.</u> , pp. 29-31 (1996). (No month)		
DN	A 12	LEHMANN, V.; "The Physics of Macropore Formation in Low Doped n-Type Silicon", <u>J. Electrochem. Soc.</u> , Vol. 140, No. 10, pp. 2836-2843 (Oct. 1993).		
DN	A 13	LEHMANN, V. et al.; "Formation Mechanism and Properties of Electrochemically Etched Trenches in n-type Silicon", <u>J. Electrochem. Soc.</u> , Vol. 137, No. 2, pp. 653-659 (Feb. 1990).		

Donald R Valente

Date Considered

6-03

- * A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).
- + An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).